

Application No.: 09/643,946

Docket No.: M4065.0166/P166-A

154. (Previously presented): The solution of claim 150, wherein said hydrofluoric acid or ammonium fluoride are configured for said selective removal by said solution in that they remain substantially in molecular form.

155. (Previously presented): The solution of claim 154, wherein said hydrochloric acid or phosphoric acid is present in sufficient amount to contribute to said hydrofluoric acid or ammonium fluoride substantially remaining in molecular form.

156. (Previously presented): The solution of claim 150, wherein said hydrofluoric acid or ammonium fluoride, said hydrochloric acid or phosphoric acid, said ethylene glycol or propylene carbonate, and said ascorbic acid are present in said solution in sufficient concentrations to suppress the solubility of aluminum fluoride.

Claim 157 (cancelled).

158. (Previously presented): A conditioning solution configured to remove residues remaining on a semiconductor substrate after a dry etch process relative to exposed metal, said conditioning solution consisting essentially of:

about 0.27% molecular HF and H₂F₂;

about 91.5% to about 97.5% propylene glycol;

about 6.5% H₂PO₄ or about 0.006% HCl;

about 0.25% citric acid; and

no more than about 2% water.

Claims 159-160 (cancelled).